

Ultrafast Power Rectifier

6 A, 600 V

RURD660S9A-F085

The RURD660S9A-F085 is an ultrafast diode with soft recovery characteristics (trr < 83 ns). It has a low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing powerloss in the switching transistors.

Features

- High Speed Switching ($t_{rr} = 63 \text{ ns (Typ.)} @ I_F = 6 \text{ A}$)
- Low Forward Voltage ($V_F = 1.26 \text{ V (Typ.)} @ I_F = 6 \text{ A}$)
- Avalanche Energy Rated
- AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Applications

- General Purpose
- Switching Mode Power Supply
- Power Switching Circuits

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

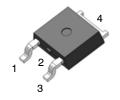
Symbol	Parameter	Ratings	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current @ $T_C = 25^{\circ}C$	6	Α
I _{FSM}	Non-repetitive Peak Surge Current	60	Α
T _J , T _{STG}	Operating Junction and Storage Temperature	- 55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

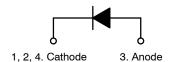
THERMAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

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Symbol	Parameter	Max	Unit	
$R_{ heta JC}$	Maximum Thermal Resistance, Junction to Case	3	°C/W	
R _{θJA} (Note 1)	Maximum Thermal Resistance, Junction to Ambient	140	°C/W	
R _{θJA} (Note 2)	Maximum Thermal Resistance, Junction to Ambient	50	°C/W	

- 1. Mounted on a minimum pad follow by JEDEC standard.
- 2. Mounted on a 1 in² pad of 2 oz copper follow by JEDEC standard.



DPAK3 (TO-252 3 LD) CASE 369AS



MARKING DIAGRAM



RUR660 = Specific Device Code \$Y = onsemi Logo &Z = Assembly Plant Code &3 = 3-Digit Date Code

&K = 2-Digits Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

RURD660S9A-F085

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Condition		Min	Тур	Max	Unit
I _R	Instantaneous Reverse	V _R = 600 V	T _C = 25°C	_	_	100	μΑ
	Current		T _C = 175°	-	-	500	μΑ
V _{FM} (Note 3)	Instantaneous Forward Voltage	I _F = 6 A	T _C = 25°C T _C = 175°	-	1.26 1.04	1.5 -	V V
t _{rr}	Reverse Recovery Time	$I_F = 1 \text{ A, di/dt} = 200 \text{ A/}\mu\text{s, V}_{CC} = 390 \text{ V}$	T _C = 25°C	-	25	33	ns
(Note 4)		$I_F = 6 \text{ A, di/dt} = 200 \text{ A/}\mu\text{s, V}_{CC} = 390 \text{ V}$	T _C = 25°C T _C = 175°	- -	63 119	83 -	ns ns
t _a t _b Qrr	Reverse Recovery Time Reverse Recovery Charge	$I_F = 6 \text{ A}, \text{ di/dt} = 200 \text{ A/}\mu\text{s}, \text{ V}_{CC} = 390 \text{ V}$	T _C = 25°C	- - -	23 40 151	- - -	ns ns nC
W _{AVL}		Avalanche Energy (L = 20 mH)		10	-	-	mJ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 3. Pulse: Test Pulse width = 300 μs, Duty Cycle = 2%
- 4. Guaranteed by design

TEST CIRCUIT AND WAVEFORMS

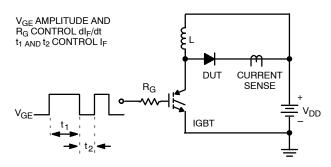


Figure 1. t_{rr} Test Circuit

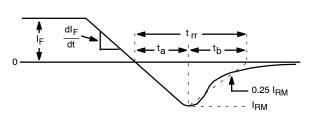


Figure 2. trr Waveforms and Definitions

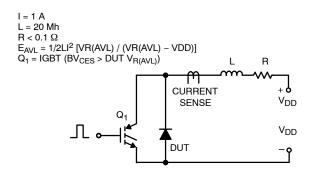


Figure 3. Avalanche Energy Test Circuit

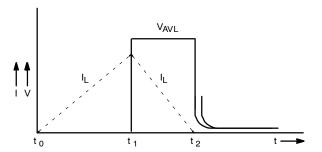
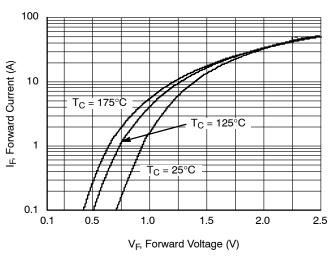


Figure 4. Avalanche Current and Voltage Waveforms

RURD660S9A-F085

TYPICAL PERFORMANCE CHARACTERISTICS

100



T_C = 175°C

T_C = 125°C

T_C = 25°C

0.01

100

200

300

400

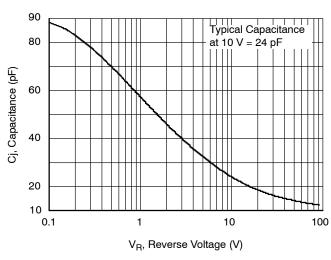
500

600

V_B, Reverse Voltage (V)

Figure 9. Typical Forward Voltage Drop vs. Forward Current

Figure 10. Typical Reverse Current vs. Reverse Voltage



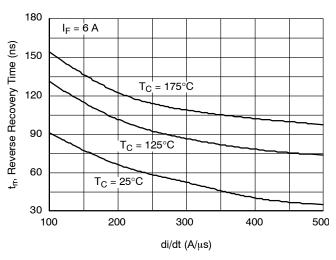
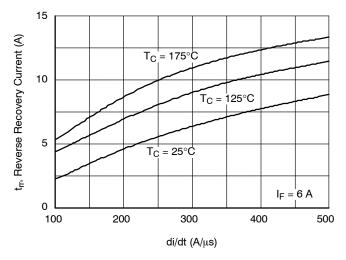


Figure 5. Typical Junction Capacitance

Figure 6. Typical Reverse Recovery Time vs. di/dt



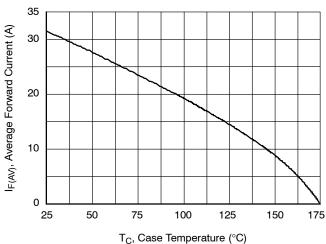


Figure 7. Typical Reverse Recovery Current vs. di/dt

Figure 8. Forward Current Derating Curve

RURD660S9A-F085

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

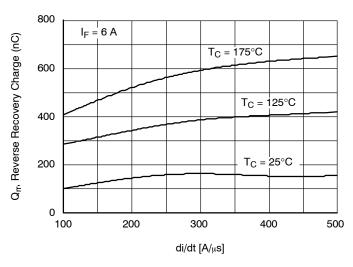


Figure 12. Reverse Recovery Charge

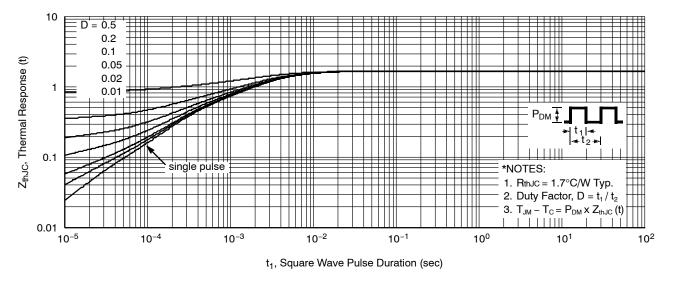


Figure 11. Transient Thermal Response Curve

ORDERING INFORMATION

Device	Device Marking	Package	Shipping [†]
RURD660S9A-F085	RUR660	TO-252 3 LD (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS **ISSUE B**

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DATE 20 DEC 2023

- NOTES: UNLESS OTHERWISE SPECIFIED

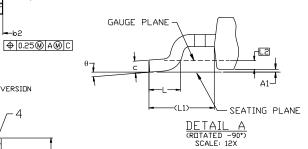
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.

 B) ALL DIMENSIONS ARE IN MILLIMETERS.

 C) DIMENSIONING AND TOLERANCING PER

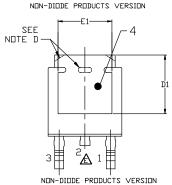
A

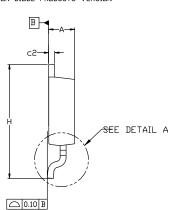
- F)
- DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M-2018.
 SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
 CORNERS OR EDGE PROTRUSION.
 FOR DIGDE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY
 STUB WITHOUT CENTER LEAD.
 DIMENSIONS ARE EXCLUSIVE OF BURRS,
 MOLD FLASH AND TIE BAR EXTRUSIONS.
 LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
 T0228P991X239-3N.



MILLIME LEKS			
MIN.	N□M.	MAX.	
2.18	2.29	2.39	
0.00	-	0.127	
0.64	0.77	0.89	
0.76	0.95	1.14	
5.21	5.34	5.46	
0.45	0.53	0.61	
0.45	0.52	0.58	
5.97	6.10	6.22	
5.21			
6.35	6.54	6.73	
4.32			
2.286 BSC			
4.572 BSC			
9.40	9.91	10.41	
1.40	1.59	1.78	
2.90 REF			
0.51 BSC			
0.89	1.08	1.27	
		1.02	
0*		10°	
	MIN. 2.18 0.00 0.64 0.76 5.21 0.45 0.45 5.97 5.21 6.35 4.32 2.6 4.5 9.40 1.40	MIN. N□M. 2.18 2.29 0.00 - 0.64 0.77 0.76 0.95 5.21 5.34 0.45 0.52 5.97 6.10 5.21 6.35 6.54 4.32 2.≥88 BS 4.57≥ BS 9.40 9.91 1.40 1.59 2.90 RE 0.51 BS	

MILL IMETERS





-5.55	MIN-
6.40	6.50 MIN
	2.85 MIN
4.5	1.25 MIN 2.286

LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON DUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE ON SEMICONDUCTOR
SOLDERING AND MOUNTING TECHNIQUES
REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXXXX XXXXXX **AYWWZZ**

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code

= Assembly Location Α

Υ = Year

WW = Work Week

77 = Assembly Lot Code

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